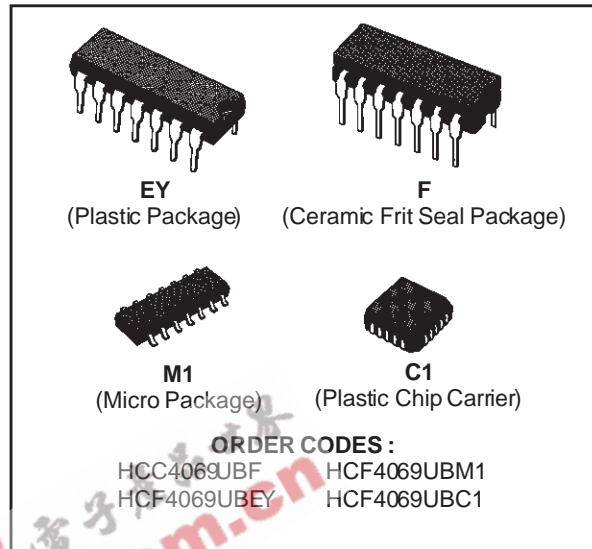


HEX INVERTER

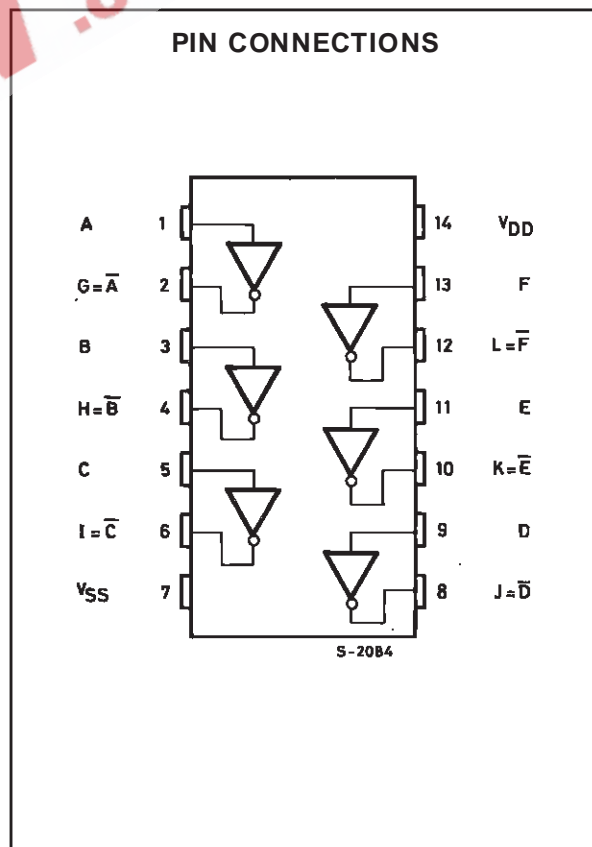
- MEDIUM-SPEED OPERATION
  - $t_{PHL}$ ,  $t_{PLH}$  = 30ns (typ.) AT 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



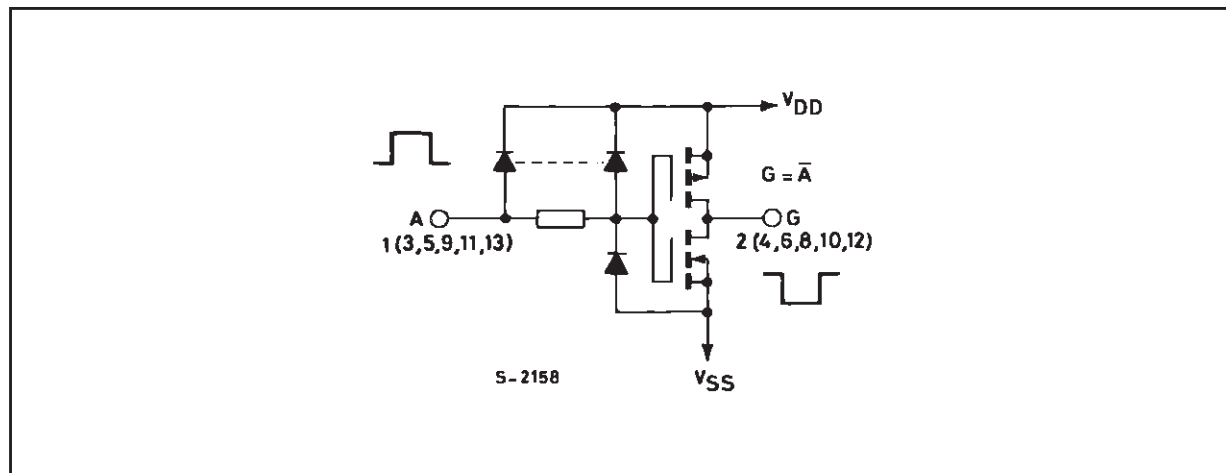
**DESCRIPTION**

The **HCC4069UB** (extended temperature range) and **HCF4069UB** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4069UB** consists of six COS/MOS inverter circuits. This device is intended for all general-purpose inverter applications where the medium-power TTL-drive and logic-level-conversion capabilities of circuits such as **HCC/HCF4049B** Hex Inverter/Buffers are not required.



**SCHEMATIC DIAGRAM OF ONE OF SIX IDENTICAL INVERTERS.**



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage : <b>HCC</b> Types	- 0.5 to + 20	V
	<b>HCF</b> Types	- 0.5 to + 18	V
V <sub>i</sub>	Input Voltage	- 0.5 to V <sub>DD</sub> + 0.5	V
I <sub>I</sub>	DC Input Current (any one input)	± 10	mA
P <sub>tot</sub>	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T <sub>op</sub> = Full Package-temperature Range	100	mW
T <sub>op</sub>	Operating Temperature : <b>HCC</b> Types	- 55 to + 125	°C
	<b>HCF</b> Types	- 40 to + 85	°C
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

\* All voltage values are referred to V<sub>SS</sub> pin voltage.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage : <b>HCC</b> Types	3 to 18	V
	<b>HCF</b> Types	3 to 15	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature : <b>HCC</b> Types	- 55 to + 125	°C
	<b>HCF</b> Types	- 40 to + 85	°C

## STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

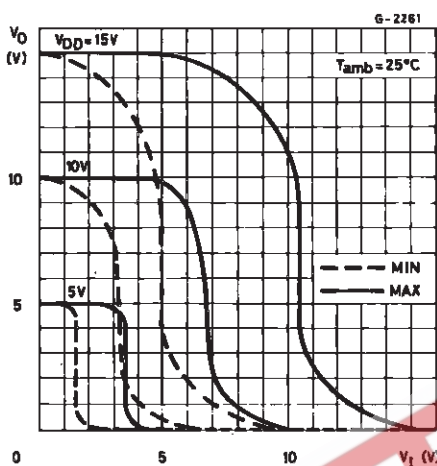
Symbol	Parameter		Test Conditions				Value						Unit	
			V <sub>I</sub> (V)	V <sub>O</sub> (V)	I <sub>O</sub>   ( $\mu$ A)	V <sub>DD</sub> (V)	T <sub>Low</sub> *		25°C			T <sub>High</sub> *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I <sub>L</sub>	Quiescent Current	HCC Types	0/ 5			5		0.25		0.01	0.25		7.5	$\mu$ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/ 5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V <sub>OH</sub>	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V <sub>OL</sub>	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V <sub>IH</sub>	Input High Voltage		0.5/4.5	< 1	5	4		4			4		V	
			1/9	< 1	10	8		8			8			
			1.5/13.5	< 1	15	12.5		12.5			12.5			
V <sub>IL</sub>	Input Low Voltage		4.5/0.5	< 1	5		1			1		1	V	
			9/1	< 1	10		2			2		2		
			13.5/1.5	< 1	15		2.5			2.5		2.5		
I <sub>OH</sub>	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4					
I <sub>OL</sub>	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage Current	HCC Types	0/18	Any Input		18		$\pm$ 0.1		$\pm$ 10 <sup>-5</sup>	$\pm$ 0.1		$\pm$ 1	
		HCF Types	0/15			15		$\pm$ 0.3		$\pm$ 10 <sup>-5</sup>	$\pm$ 0.3		$\pm$ 1	
C <sub>I</sub>	Input Capacitance		Any Input						5	7.5			pF	

\* T<sub>Low</sub> = - 55°C for HCC device : - 40°C for HCF device.\* T<sub>High</sub> = + 125°C for HCC device : + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V<sub>DD</sub> = 5V, 2V min. with V<sub>DD</sub> = 10V, 2.5V min. with V<sub>DD</sub> = 15V.

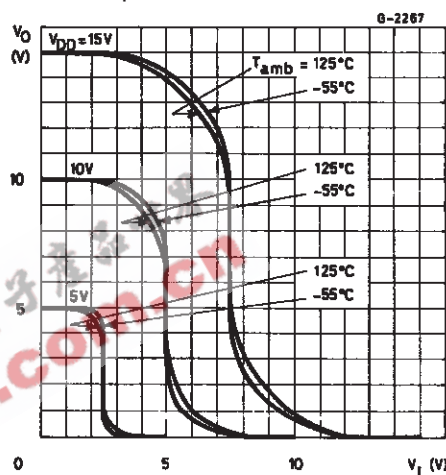
**DYNAMIC ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}\text{C}$ ,  $C_L = 50\text{pF}$ ,  $R_L = 200\text{k}\Omega$ , typical temperature coefficient for all  $V_{DD} = 0.3\%/^{\circ}\text{C}$  values, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			$V_{DD}$ (V)	Min.	Typ.	Max.	
$t_{PLH}$ , $t_{PHL}$	Propagation Delay Time		5		55	110	ns
			10		30	60	
			15		25	50	
$t_{TLH}$ , $t_{THL}$	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

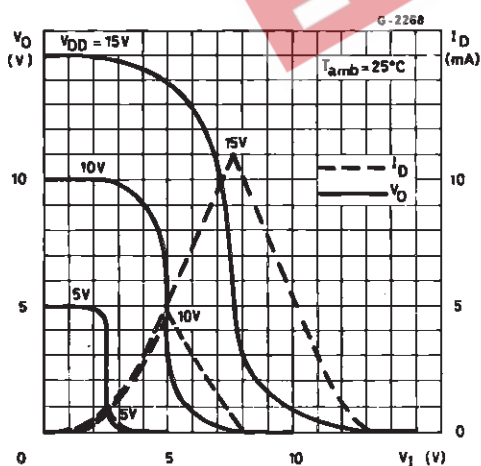
Minimum and Maximum Voltage Transfer Characteristics.



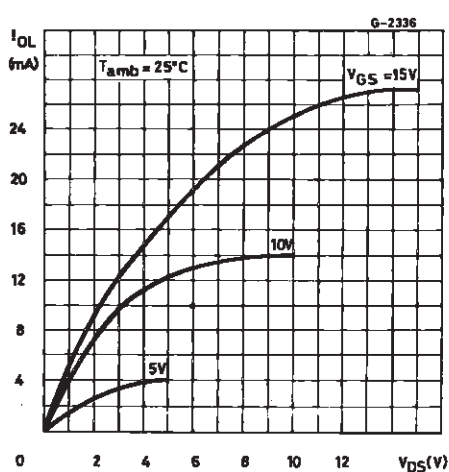
Typical Voltage Transfer Characteristics as a Function of Temperature.



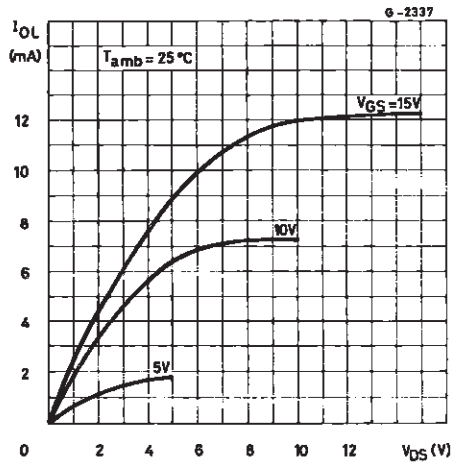
Typical Current and Voltage Transfer Characteristics.



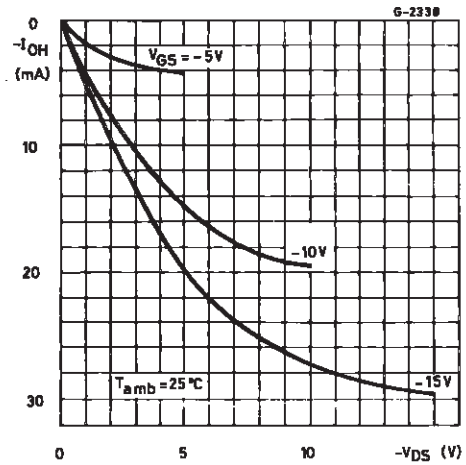
Typical Output Low (sink) Current Characteristics.



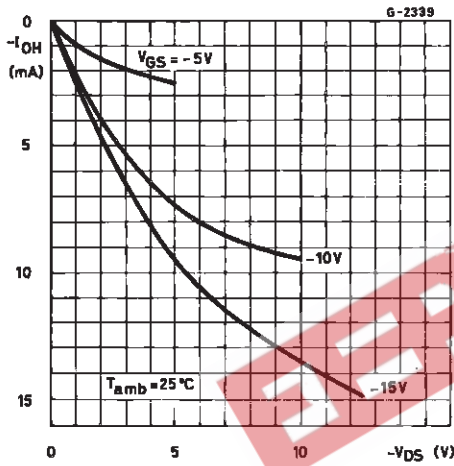
Minimum Output Low (sink) Current Characteristics.



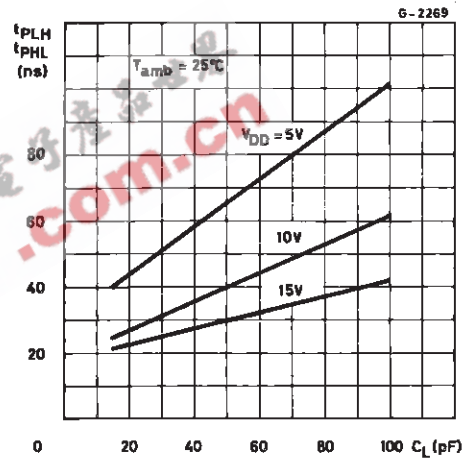
Typical Output High (source) Current Characteristics.



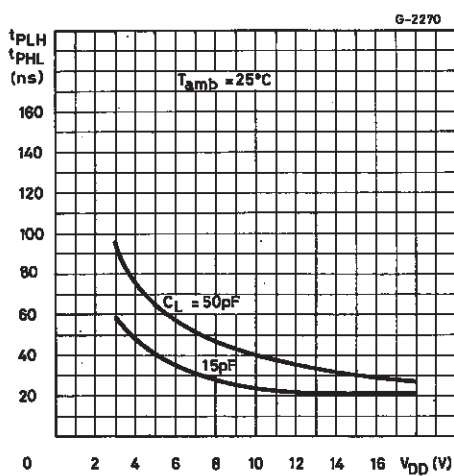
Minimum Output High (source) Current Characteristics.



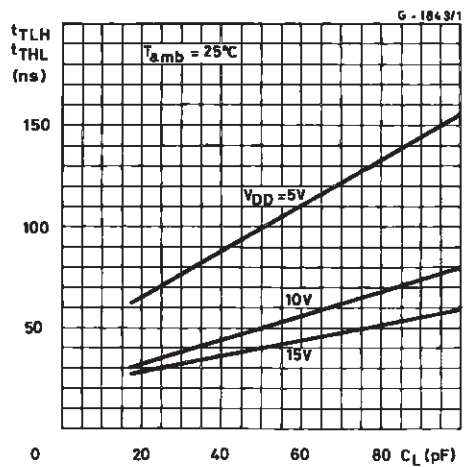
Typical Propagation Delay Time vs. Load Capacitance.



Typical Propagation Delay Time vs. Load Capacitance.

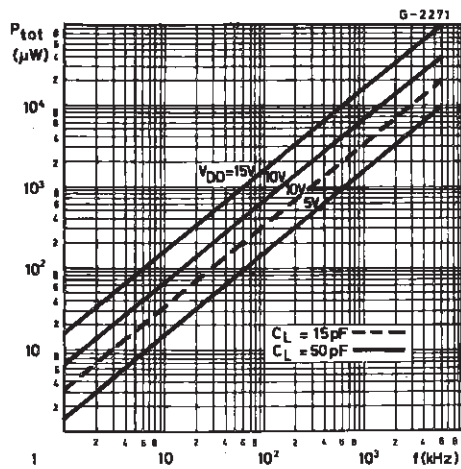


Typical Transition Time vs. Load Capacitance.

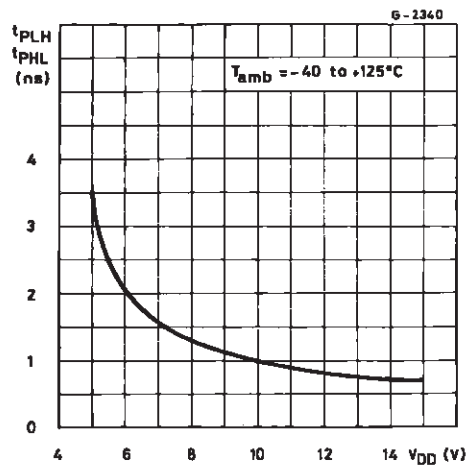


# HCC/HCF4069UB

Typical Dynamic Power Dissipation/per Inverter vs. Frequency.

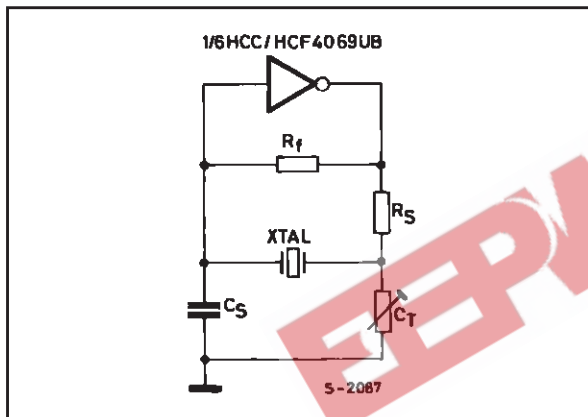


Variation of Normalized Propagation Delay Time ( $t_{PHL}$  and  $t_{PLH}$ ) with Supply Voltage.

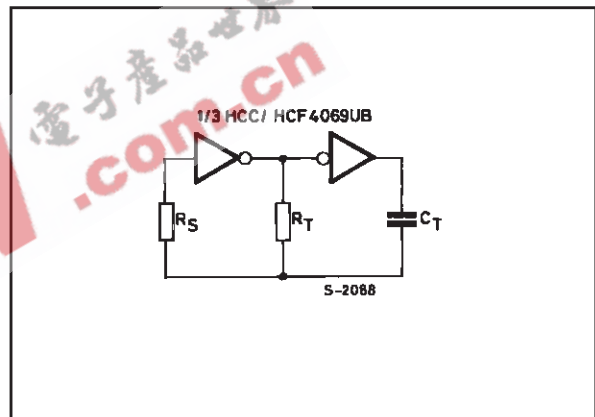


## APPLICATIONS

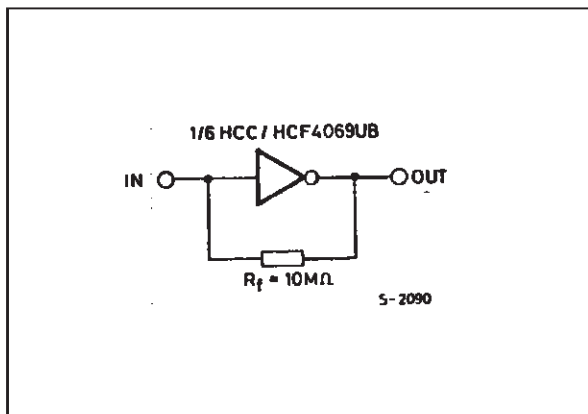
Typical Crystal Oscillator Circuit.



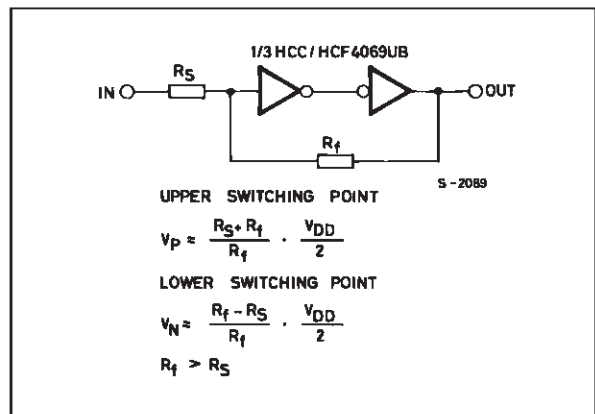
Typical RC Oscillator Circuit.



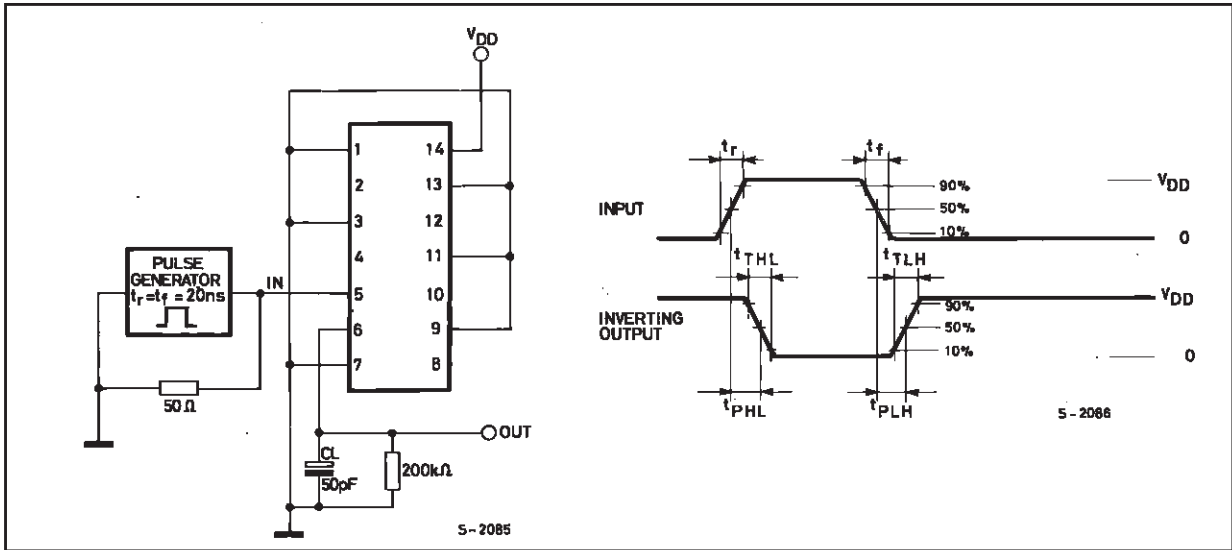
High Input Impedance Amplifier.



Input Pulse Shaping Circuit (schmitt trigger).

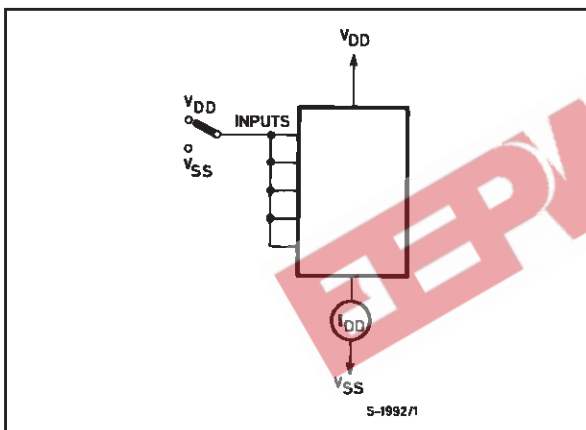


DYNAMIC ELECTRICAL CHARACTERISTICS AND WAVEFORMS

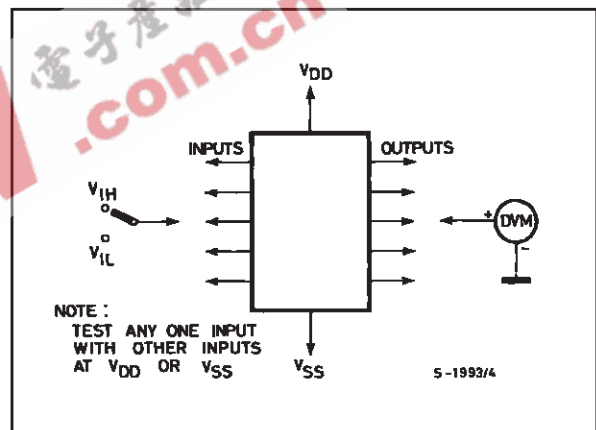


TEST CIRCUITS

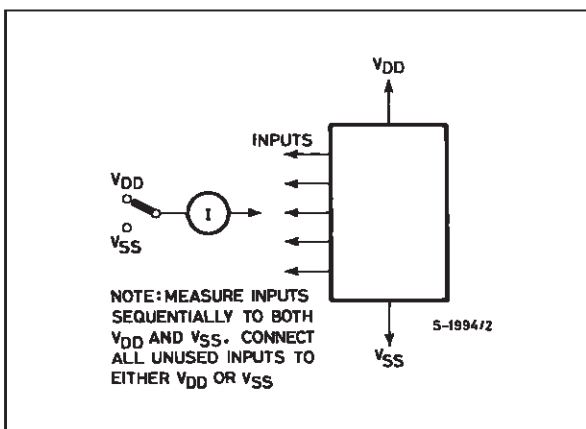
Quiescent Device Current.



Noise Immunity

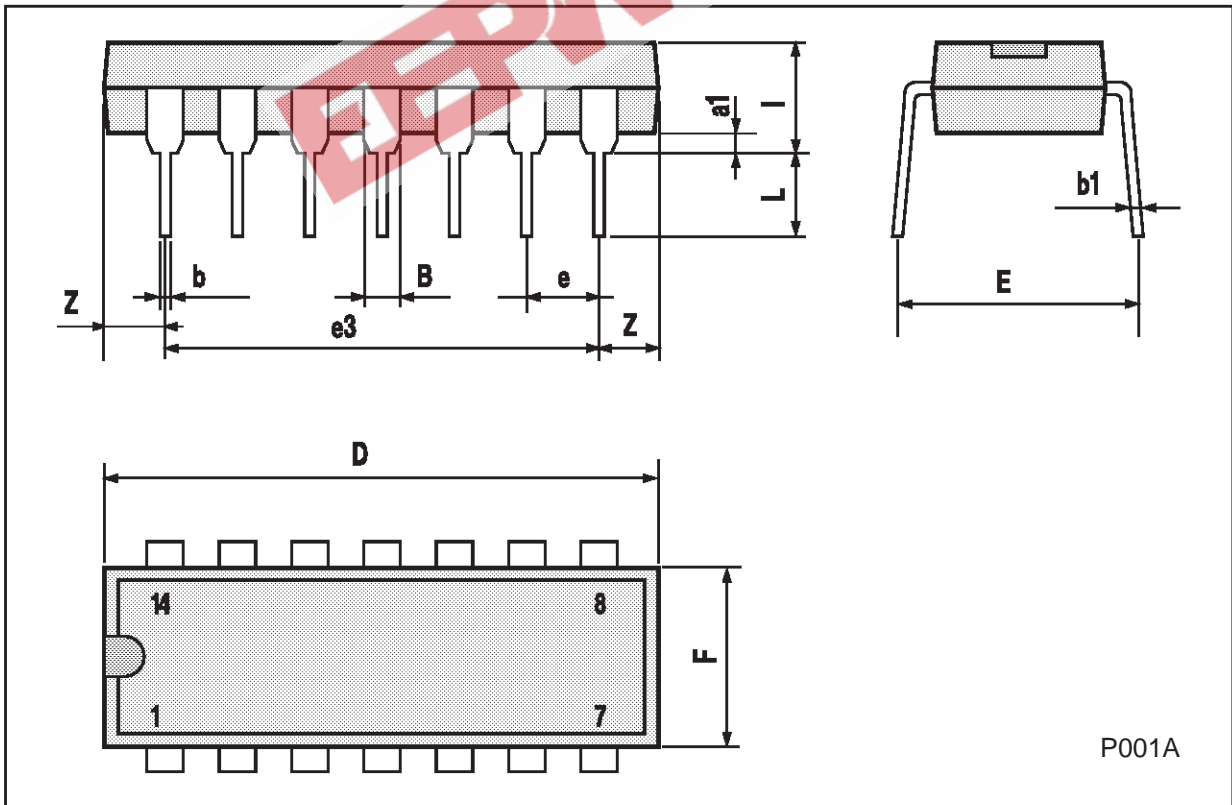


Input Leakage Current.



**Plastic DIP14 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100

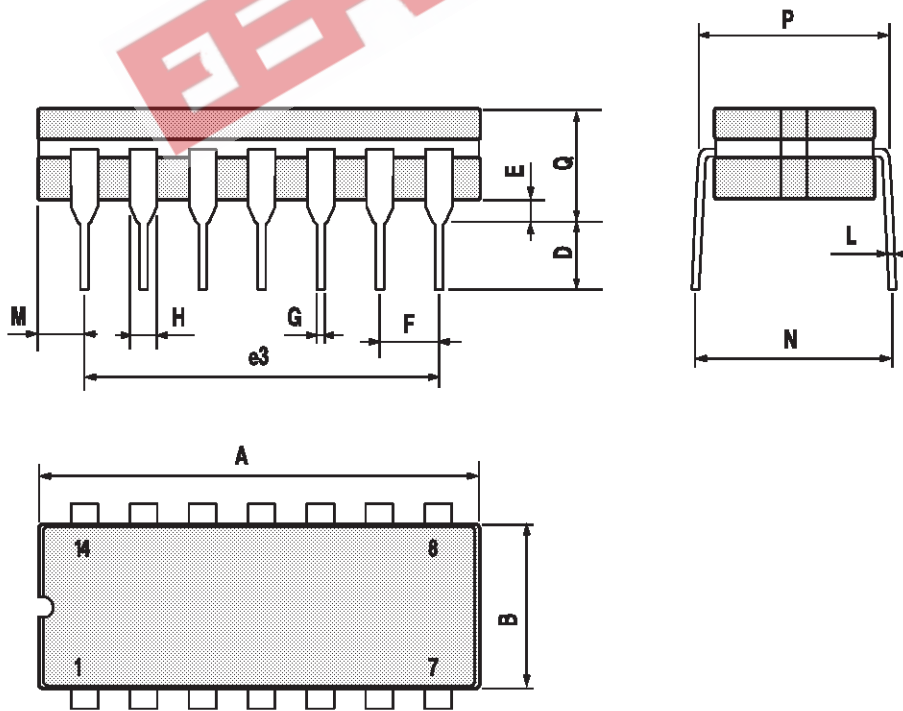


P001A



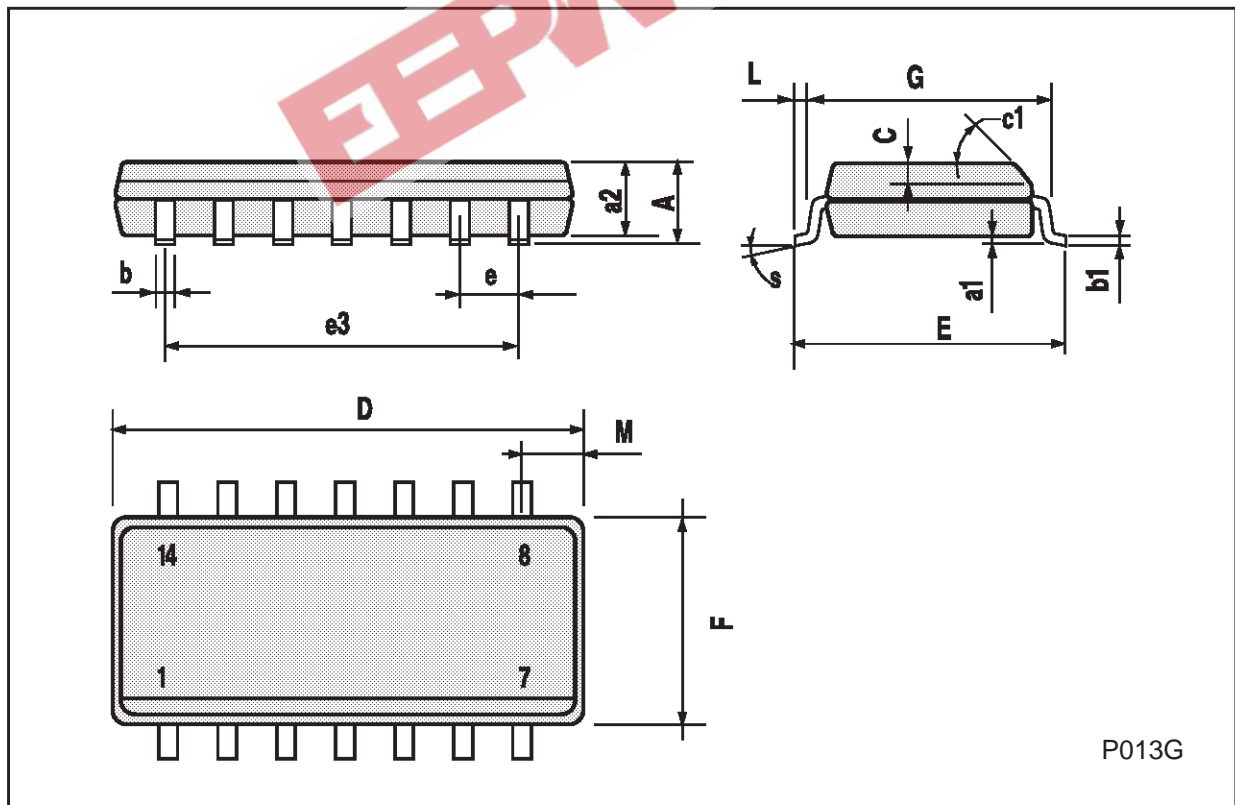
## Ceramic DIP14/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



**SO14 MECHANICAL DATA**

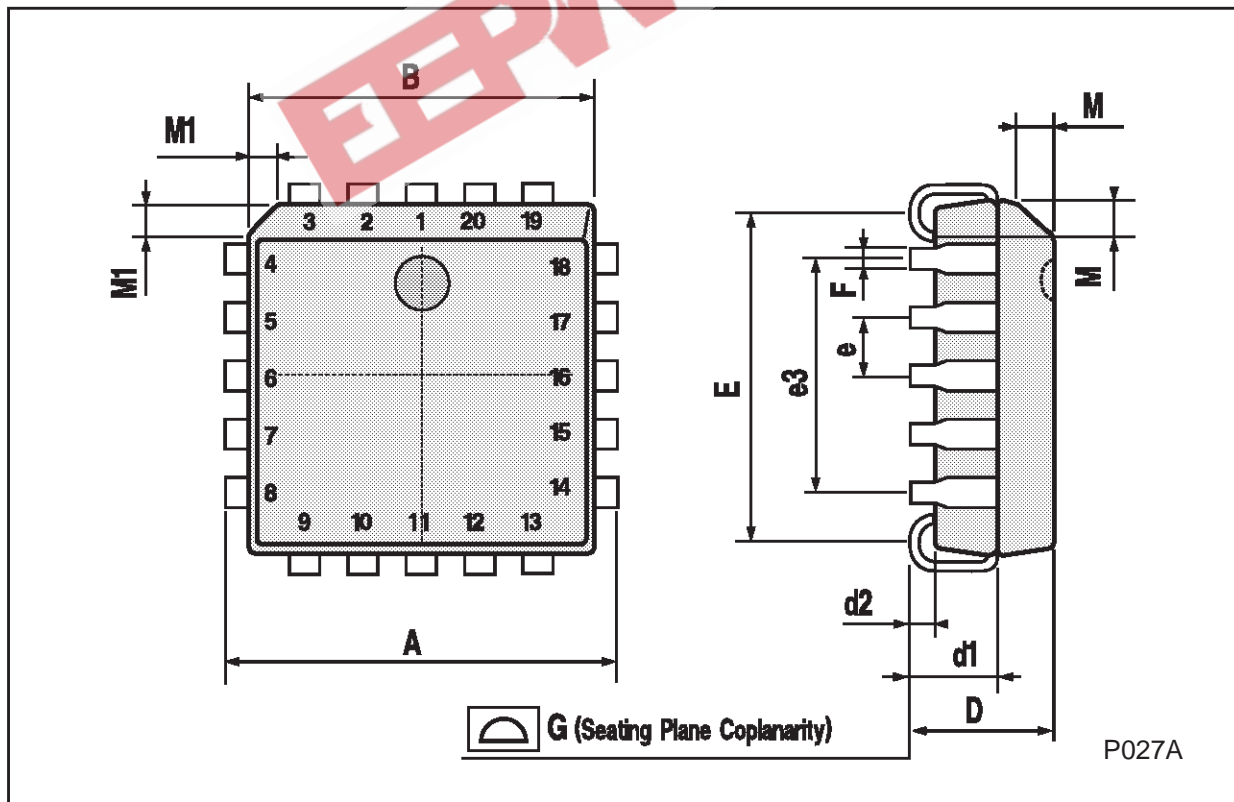
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

## PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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